

DYNAMIC MEMORY CELL AND METHOD OF MANUFACTURING SAME**ABSTRACT**

5 A memory device has a plurality of memory cells, wherein
each memory cell has a trench capacitor formed in a
semiconductor substrate and an access transistor for it.
Each access transistor has a first contact region connected
to an internal electrode of the trench capacitor, a second
10 contact region to a bit line and a control electrode
region, wherein the control electrode regions of
neighboring access transistors are connected by a word line
formed in the semiconductor substrate.